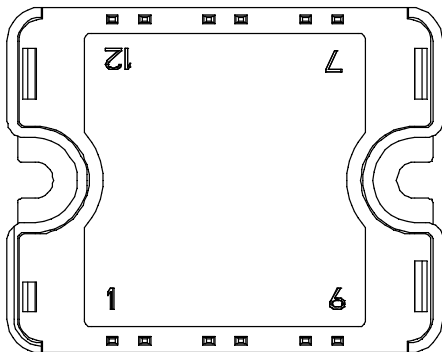
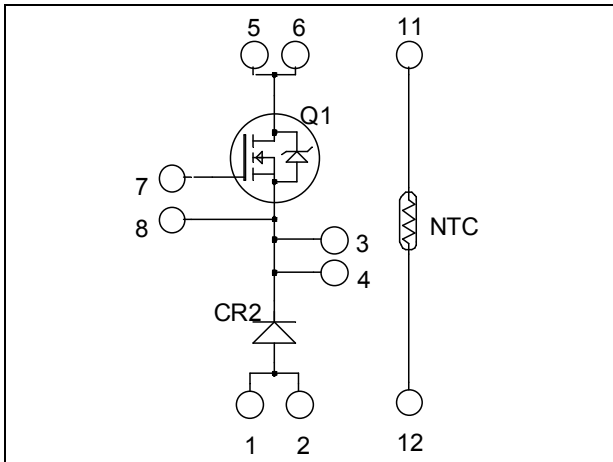


## Buck chopper Super Junction MOSFET Power Module

$V_{DSS} = 800V$   
 $R_{DSon} = 150m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 28A \text{ @ } T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- **COOLMOS**  
Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

| Symbol     | Parameter   | Max ratings        | Unit      |
|------------|---|--------------------|-----------|
| $V_{DSS}$  | Drain - Source Breakdown Voltage                  | 800                | V         |
| $I_D$      | Continuous Drain Current                          | $T_c = 25^\circ C$ | 28        |
|            |   | $T_c = 80^\circ C$ | 21        |
| $I_{DM}$   | Pulsed Drain current                              | 110                |           |
| $V_{GS}$   | Gate - Source Voltage                             | $\pm 30$           | V         |
| $R_{DSon}$ | Drain - Source ON Resistance                      | 150                | $m\Omega$ |
| $P_D$      | Maximum Power Dissipation                         | $T_c = 25^\circ C$ | 277       |
| $I_{AR}$   | Avalanche current (repetitive and non repetitive) | 17                 | A         |
| $E_{AR}$   | Repetitive Avalanche Energy                       | 0.5                | mJ        |
| $E_{AS}$   | Single Pulse Avalanche Energy                     | 670                |           |

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

| Symbol              | Characteristic                  | Test Conditions  | Min                    | Typ | Max | Unit |    |
|---------------------|---------------------------------|--|------------------------|-----|-----|------|----|
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 800V             | T <sub>j</sub> = 25°C  |     |     | 50   | μA |
|                     |                                 | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 800V             | T <sub>j</sub> = 125°C |     |     | 375  |    |
| R <sub>DS(on)</sub> | Drain – Source on Resistance    | V <sub>GS</sub> = 10V, I <sub>D</sub> = 14A              |                        |     |     | 150  | mΩ |
| V <sub>GS(th)</sub> | Gate Threshold Voltage          | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 2mA |                        | 2.1 | 3   | 3.9  | V  |
| I <sub>GSS</sub>    | Gate – Source Leakage Current   | V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0V            |                        |     |     | ±150 | nA |

**Dynamic Characteristics**

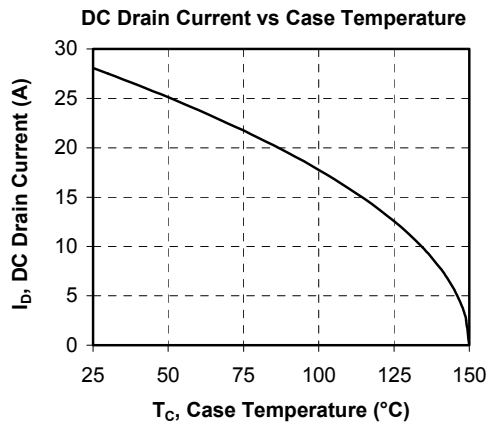
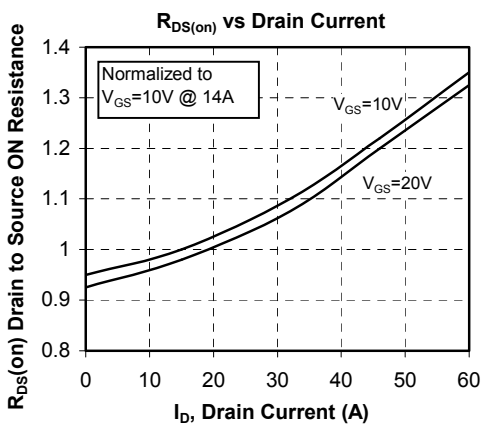
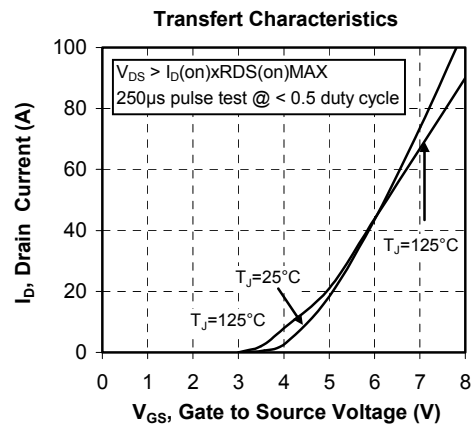
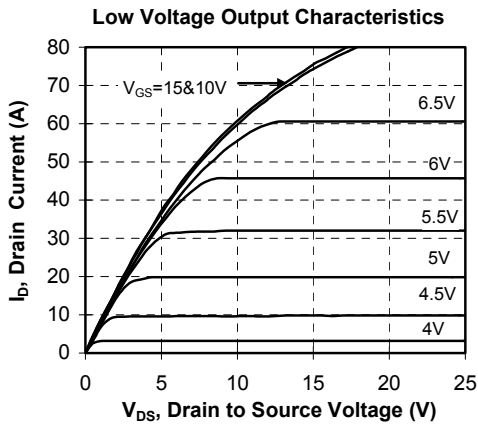
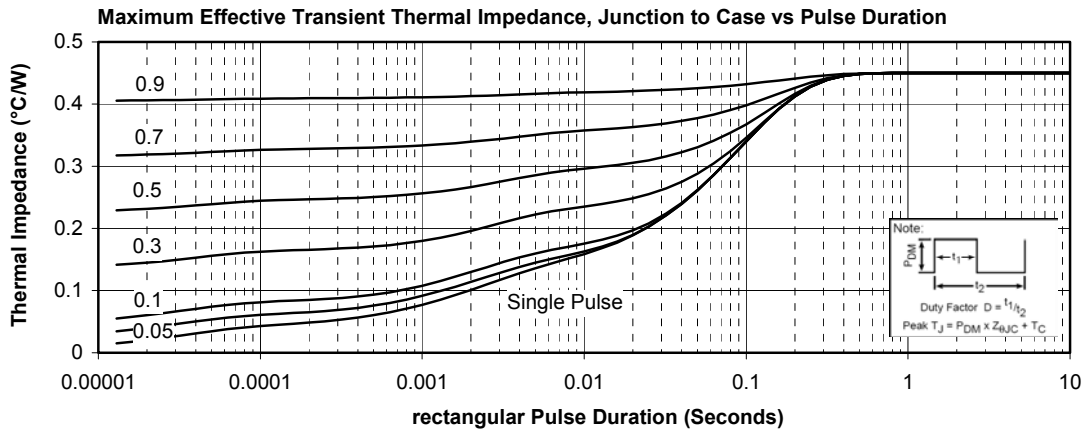
| Symbol              | Characteristic               | Test Conditions  | Min | Typ  | Max | Unit |
|---------------------|------------------------------|--|-----|------|-----|------|
| C <sub>iss</sub>    | Input Capacitance            | V <sub>GS</sub> = 0V<br>V <sub>DS</sub> = 25V<br>f = 1MHz  |     | 4507 |     | pF   |
| C <sub>oss</sub>    | Output Capacitance           |  |     | 2092 |     |      |
| C <sub>rss</sub>    | Reverse Transfer Capacitance |  |     | 108  |     |      |
| Q <sub>g</sub>      | Total gate Charge            | V <sub>GS</sub> = 10V<br>V <sub>Bus</sub> = 400V<br>I <sub>D</sub> = 28A   |     | 180  |     | nC   |
| Q <sub>gs</sub>     | Gate – Source Charge         |  |     | 22   |     |      |
| Q <sub>gd</sub>     | Gate – Drain Charge          |  |     | 90   |     |      |
| T <sub>d(on)</sub>  | Turn-on Delay Time           | <b>Inductive switching @125°C</b><br>V <sub>GS</sub> = 15V<br>V <sub>Bus</sub> = 533V<br>I <sub>D</sub> = 28A<br>R <sub>G</sub> = 2.5Ω |     | 10   |     | ns   |
| T <sub>r</sub>      | Rise Time                    |  |     | 13   |     |      |
| T <sub>d(off)</sub> | Turn-off Delay Time          |  |     | 83   |     |      |
| T <sub>f</sub>      | Fall Time                    |  |     | 35   |     |      |
| E <sub>on</sub>     | Turn-on Switching Energy     | <b>Inductive switching @ 25°C</b><br>V <sub>GS</sub> = 15V, V <sub>Bus</sub> = 533V<br>I <sub>D</sub> = 28A, R <sub>G</sub> = 2.5Ω     |     | 486  |     | μJ   |
| E <sub>off</sub>    | Turn-off Switching Energy    |  |     | 278  |     |      |
| E <sub>on</sub>     | Turn-on Switching Energy     | <b>Inductive switching @ 125°C</b><br>V <sub>GS</sub> = 15V, V <sub>Bus</sub> = 533V<br>I <sub>D</sub> = 28A, R <sub>G</sub> = 2.5Ω    |     | 850  |     | μJ   |
| E <sub>off</sub>    | Turn-off Switching Energy    |  |     | 342  |     |      |

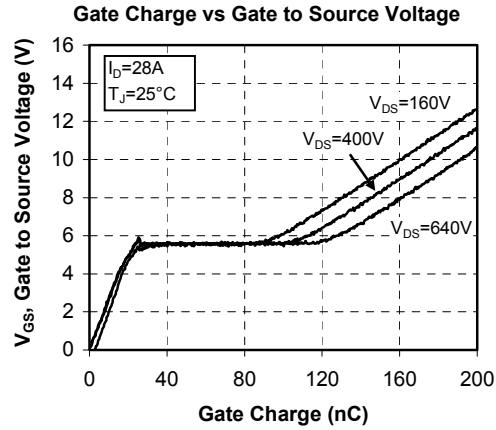
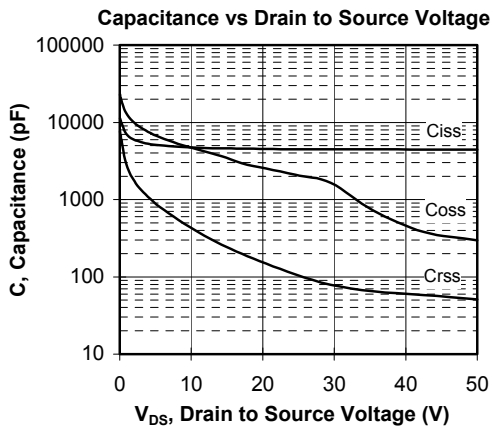
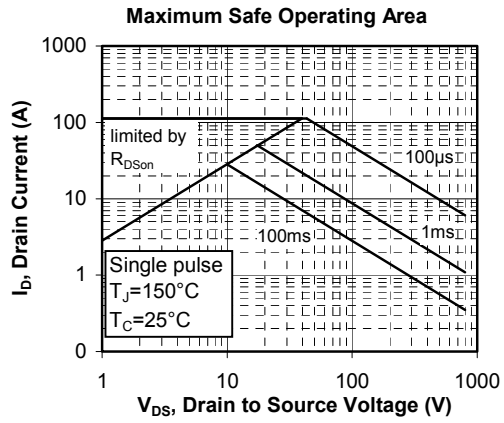
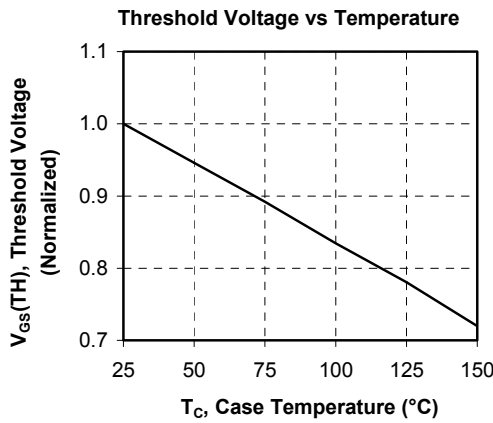
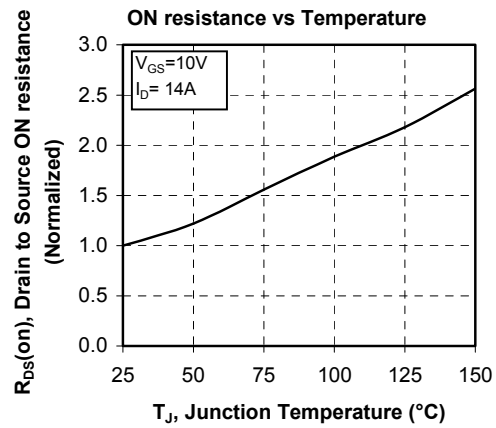
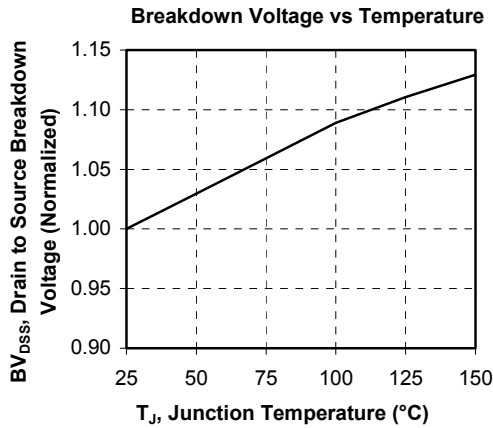
**Chopper diode ratings and characteristics**

| Symbol           | Characteristic                          | Test Conditions  | Min                    | Typ  | Max | Unit |
|------------------|---|--|------------------------|------|-----|------|
| V <sub>RRM</sub> | Maximum Peak Repetitive Reverse Voltage |  | 1200                   |      |     | V    |
| I <sub>RM</sub>  | Maximum Reverse Leakage Current         | V <sub>R</sub> = 1200V   | T <sub>j</sub> = 25°C  |      | 100 | μA   |
|                  |   |  | T <sub>j</sub> = 125°C |      | 500 |      |
| I <sub>F</sub>   | DC Forward Current                      | T <sub>c</sub> = 80°C  |                        | 30   |     | A    |
| V <sub>F</sub>   | Diode Forward Voltage                   | I <sub>F</sub> = 30A   |                        | 2.6  | 3.1 | V    |
|                  |   | I <sub>F</sub> = 60A   |                        | 3.2  |     |      |
|                  |   | I <sub>F</sub> = 30A   | T <sub>j</sub> = 125°C | 1.8  |     |      |
| t <sub>rr</sub>  | Reverse Recovery Time                   | I <sub>F</sub> = 30A<br>V <sub>R</sub> = 800V<br>di/dt = 200A/μs | T <sub>j</sub> = 25°C  | 300  |     | ns   |
|                  |   |  | T <sub>j</sub> = 125°C | 380  |     |      |
| Q <sub>rr</sub>  | Reverse Recovery Charge                 | I <sub>F</sub> = 30A<br>V <sub>R</sub> = 800V<br>di/dt = 200A/μs | T <sub>j</sub> = 25°C  | 360  |     | nC   |
|                  |   |  | T <sub>j</sub> = 125°C | 1700 |     |      |

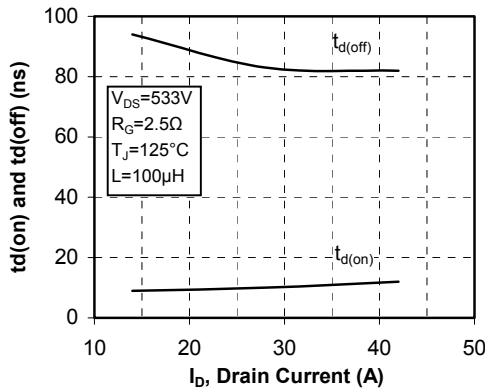


## Typical Performance Curve

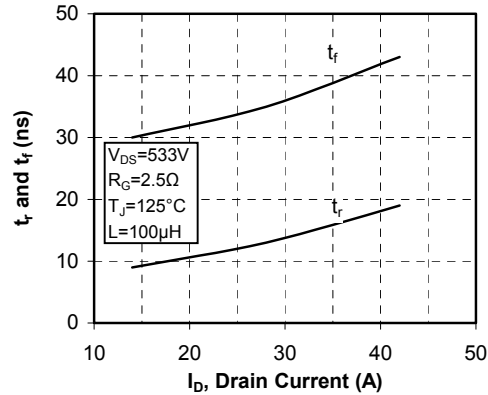




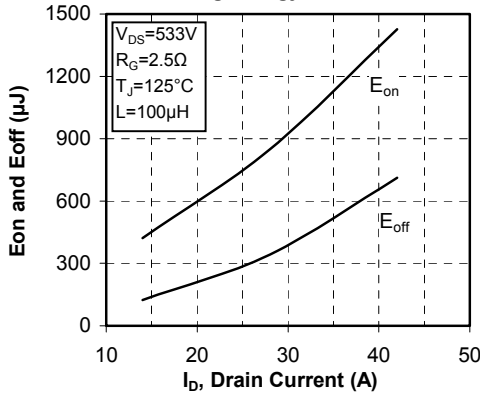
Delay Times vs Current



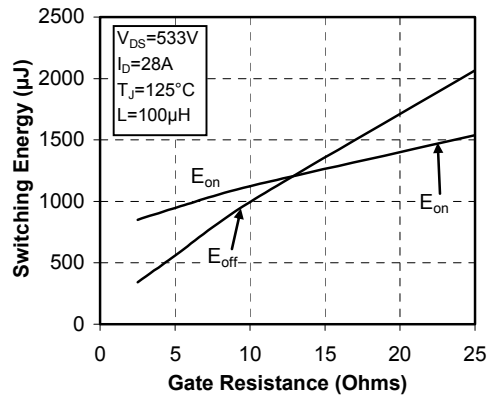
Rise and Fall times vs Current



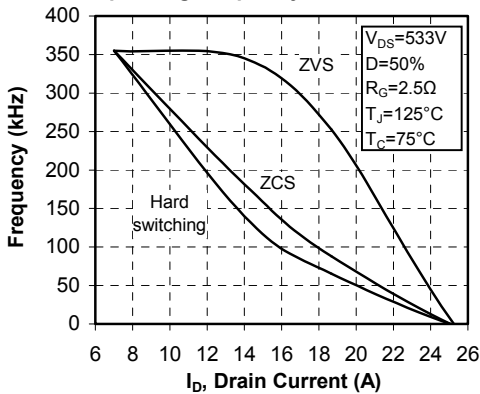
Switching Energy vs Current



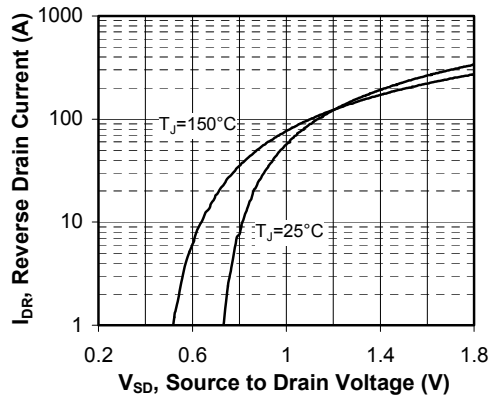
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



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